Product data sheet

1. General description

NPN/NPN Resistor-Equipped Transistors (RET) in a leadless ultra small DFN1010B-6 (SOT1216) Surface-Mounted Device (SMD) plastic package.

PNP/PNP complement: PQMB11.

NPN/PNP complement: PQMD3.

2. Features and benefits

- 100 mA output current capability
- Built-in bias resistors
- · Simplifies circuit design
- Low package height of 0.37 mm
- Reduces component count
- Reduces pick and place costs
- AEC-Q101 qualified

3. Applications

- Low current peripheral driver
- Control of IC inputs
- Replaces general-purpose transistors in digital applications
- Mobile applications

4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Тур	Max	Unit	
Per transistor	Per transistor							
V _{CEO}	collector-emitter voltage	open base		-	-	50	V	
Io	output current			-	-	100	mA	
Per transistor							,	
R1	bias resistor 1	T _{amb} = 25 °C	[1]	7	10	13	kΩ	
R2/R1	bias resistor ratio			0.8	1	1.2		

[1] See section "Test information" for resistor calculation and test conditions.





NPN/NPN resistor-equipped transistors; R1 = 10 k Ω , R2 = 10 k Ω

5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	GND1	GND (emitter) TR1	500	O1 I2 GND2
2	I1	input (base) TR1	$\begin{bmatrix} 1 \\ 7 \end{bmatrix} \begin{bmatrix} 6 \\ \end{bmatrix}$	
3	O2	output (collector) TR2	2 5	R1 R2
4	GND2	GND (emitter) TR2		TR1 TR2
5	12	input (base) TR2	3 8 4	R2 R1
6	O1	output (collector) TR1	Transparent top view	
7	O1	output (collector) TR1	DFN1010B-6 (SOT1216)	GND1 I1 O2 aaa-019894
8	O2	output (collector) TR2		dad 675557

6. Ordering information

Table 3. Ordering information

Type number	Package					
	Name	Description	Version			
PQMH11	DFN1010B-6	DFN1010B-6: plastic thermal enhanced ultra thin small outline package; no leads; 6 terminals	SOT1216			

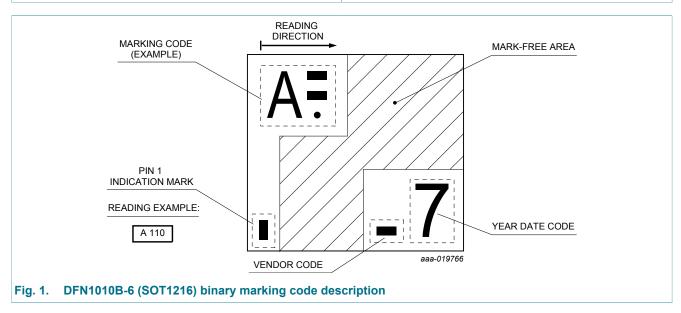
2/14

NPN/NPN resistor-equipped transistors; R1 = 10 k Ω , R2 = 10 k Ω

7. Marking

Table 4. Marking codes

Type number	Marking code
PQMH11	A 001



NPN/NPN resistor-equipped transistors; R1 = 10 k Ω , R2 = 10 k Ω

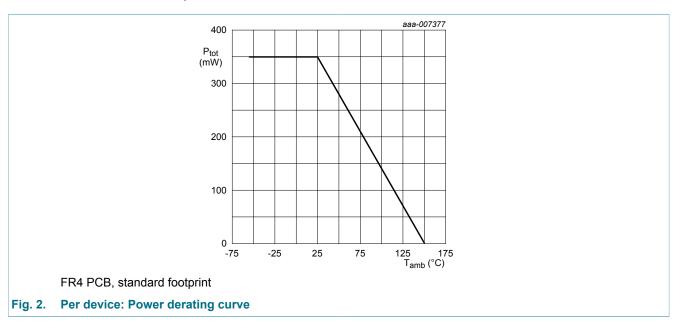
8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
Per transis	tor	'	'			
V _{CBO}	collector-base voltage	open emitter		-	50	V
V _{CEO}	collector-emitter voltage	open base		-	50	V
V _{EBO}	emitter-base voltage	open collector		-	10	V
V _I inpu	input voltage	positive		-	40	V
		negative		-	-10	V
Io	output current			-	100	mA
I _{CM}	peak collector current			-	100	mA
P _{tot}	total power dissipation	T _{amb} ≤ 25 °C	[1]	-	230	mW
Per device		1	'	'		
P _{tot}	total power dissipation	T _{amb} ≤ 25 °C	[1]	-	350	mW
T _j	junction temperature			-	150	°C
T _{amb}	ambient temperature			-55	150	°C
T _{stg}	storage temperature			-65	150	°C

[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.



PQMH11

NPN/NPN resistor-equipped transistors; R1 = 10 k Ω , R2 = 10 k Ω

9. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
Per transiste	or						
$R_{\text{th(j-a)}}$	thermal resistance from junction to ambient	in free air	[1]	-	-	543	K/W
Per device							
$R_{\text{th(j-a)}}$	thermal resistance from junction to ambient	in free air	[1]	-	-	357	K/W

[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

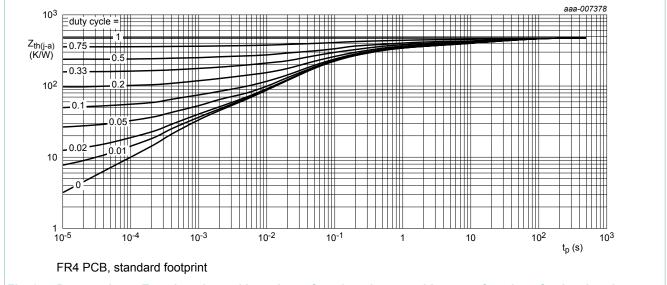


Fig. 3. Per transistor: Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

NPN/NPN resistor-equipped transistors; R1 = 10 k Ω , R2 = 10 k Ω

10. Characteristics

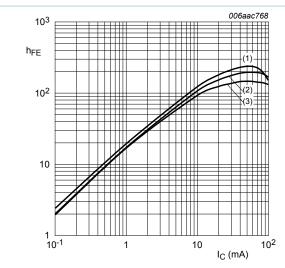
Table 7. Characteristics

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
Per transist	or						
I _{CBO}	collector-base cut-off current (emitter open)	V _{CB} = 50 V; I _E = 0 A; T _{amb} = 25 °C		-	-	100	nA
I _{CEO}	collector-emitter cut-off	V _{CE} = 30 V; I _B = 0 A; T _{amb} = 25 °C		-	-	1	μA
	current (base open)	V _{CE} = 30 V; I _B = 0 A; T _{amb} = 150 °C		-	-	5	μA
I _{EBO}	emitter-base cut-off current (collector open)	$V_{EB} = 5 \text{ V}; I_{C} = 0 \text{ A}; T_{amb} = 25 \text{ °C}$		-	-	400	μA
h _{FE}	DC current gain	V _{CE} = 5 V; I _C = 5 mA; T _{amb} = 25 °C		30	-	-	
V _{CEsat}	collector-emitter saturation voltage	$I_C = 10 \text{ mA}; I_B = 0.5 \text{ mA}; T_{amb} = 25 \text{ °C}$		-	-	150	mV
$V_{I(off)}$	off-state input voltage	V_{CE} = 5 V; I_{C} = 100 μ A; T_{amb} = 25 °C		-	1.1	0.8	V
$V_{I(on)}$	on-state input voltage	V_{CE} = 0.3 V; I_{C} = 10 mA; T_{amb} = 25 °C		2.5	1.8	-	V
R1	bias resistor 1	T _{amb} = 25 °C	[1]	7	10	13	kΩ
R2/R1	bias resistor ratio		[1]	0.8	1	1.2	
C _C	collector capacitance	V_{CB} = 10 V; I_{E} = 0 A; f = 1 MHz; T_{amb} = 25 °C		-	-	2.5	pF
f _T	transition frequency	$V_{CE} = 5 \text{ V; } I_{C} = 10 \text{ mA; } f = 100 \text{ MHz;}$ $T_{amb} = 25 \text{ °C}$	[2]	-	230	-	MHz

^[1] See section "Test information" for resistor calculation and test conditions.

^[2] Characteristics of built-in transistor

NPN/NPN resistor-equipped transistors; R1 = 10 k Ω , R2 = 10 k Ω



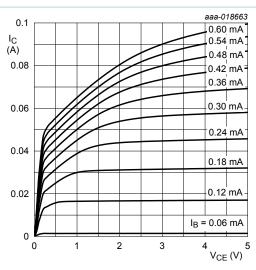
$$V_{CE} = 5 V$$

(1)
$$T_{amb} = 100 \, ^{\circ}C$$

(2)
$$T_{amb} = 25 \, ^{\circ}C$$

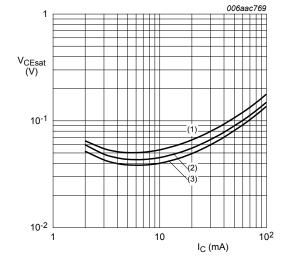
(3)
$$T_{amb} = -40 \, ^{\circ}C$$

Fig. 4. DC current gain as a function of collector current; typical values



 $T_{amb} = 25 \, ^{\circ}C$

Fig. 5. Collector current as a function of collectoremitter voltage; typical values



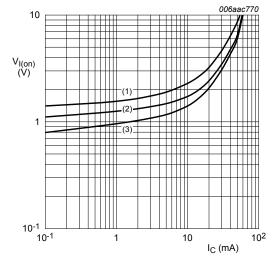
$$I_{\rm C}/I_{\rm B} = 20$$

(1)
$$T_{amb} = 100 \, ^{\circ}C$$

(2)
$$T_{amb}$$
 = 25 °C

(3)
$$T_{amb} = -40 \, ^{\circ}C$$

Fig. 6. Collector-emitter saturation voltage as a function of collector current; typical values



$$V_{CE} = 0.3 \text{ V}$$

(1)
$$T_{amb} = -40 \, ^{\circ}C$$

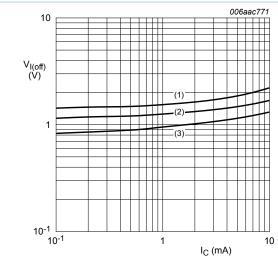
(2)
$$T_{amb}$$
 = 25 °C

(3)
$$T_{amb} = 100 \, ^{\circ}C$$

Fig. 7. On-state input voltage as a function of collector current; typical values

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NPN/NPN resistor-equipped transistors; R1 = 10 k Ω , R2 = 10 k Ω



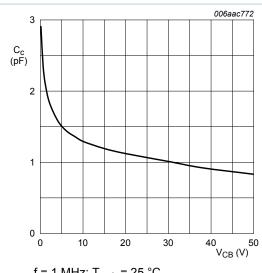
$$V_{CE} = 5 V$$

(1)
$$T_{amb} = -40 \, ^{\circ}C$$

(2)
$$T_{amb} = 25 \, ^{\circ}C$$

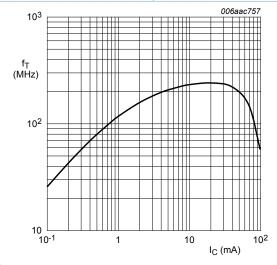
(3) $T_{amb} = 100 \, ^{\circ}C$

Fig. 8. Off-state input voltage as a function of collector current; typical values



 $f = 1 MHz; T_{amb} = 25 °C$

Fig. 9. Collector capacitance as a function of collectorbase voltage; typical values



 V_{CE} = 5 V; T_{amb} = 25 °C

Fig. 10. Transition frequency as a function of collector current; typical values of built-in transistor

11. Test information

11.1 Quality information

This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard Q101 - Stress test qualification for discrete semiconductors, and is suitable for use in automotive applications.

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NPN/NPN resistor-equipped transistors; R1 = 10 k Ω , R2 = 10 k Ω

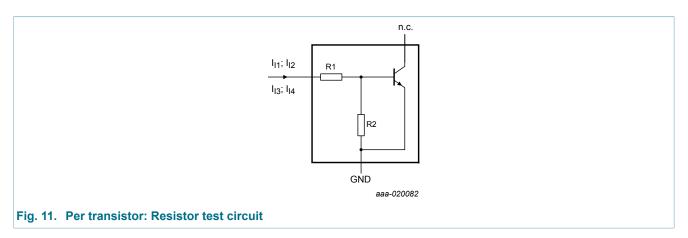
11.2 Resistor calculation

Calculation of bias resistor 1 (R1)

$$R1 = \frac{V(I12) - V(I11)}{I12 - I11}$$

Calculation of bias resistor ratio (R2/R1)

$$\frac{R2}{R1} = \frac{V(I14) - V(I13)}{R1 \cdot (I14 - I13)} - 1$$

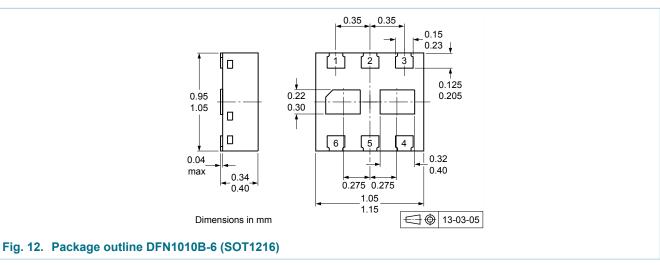


11.3 Resistor test conditions

Table 8. Resistor test conditions

R1 (kΩ)	R2 (kΩ)	Test conditions			
		I _{I1}	I _{I2}	I _{I3}	I ₁₄
10	10	350 μΑ	450 μΑ	-350 μΑ	-450 μΑ

12. Package outline

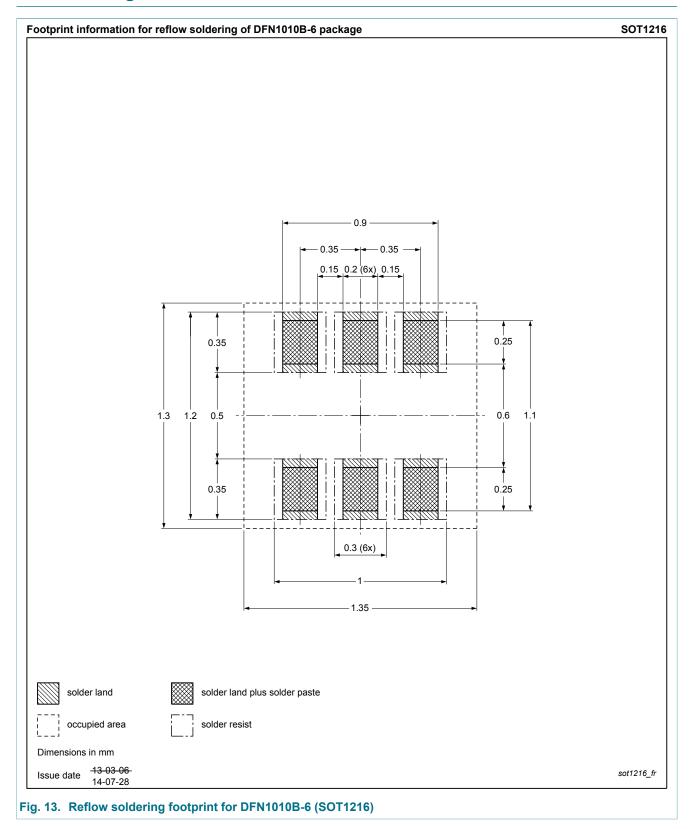


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NPN/NPN resistor-equipped transistors; R1 = 10 k Ω , R2 = 10 k Ω

13. Soldering



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14. Revision history

Table 9. Revision history

Data sheet ID	Release date	Data sheet status	Change notice	Supersedes
PQMH11 v.1	20151026	Product data sheet	-	-

NPN/NPN resistor-equipped transistors; R1 = 10 k Ω , R2 = 10 k Ω

15. Legal information

15.1 Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
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NPN/NPN resistor-equipped transistors; R1 = 10 k Ω , R2 = 10 k Ω

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NPN/NPN resistor-equipped transistors; R1 = 10 k Ω , R2 = 10 k Ω

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